FIG. 1

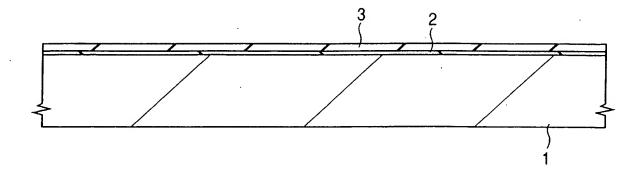
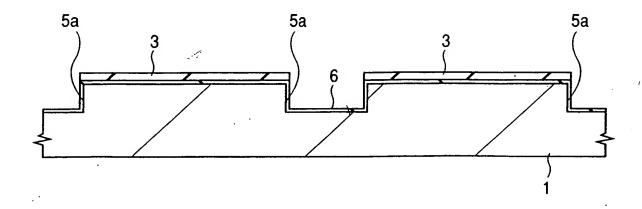


FIG. 2

FIG. 3



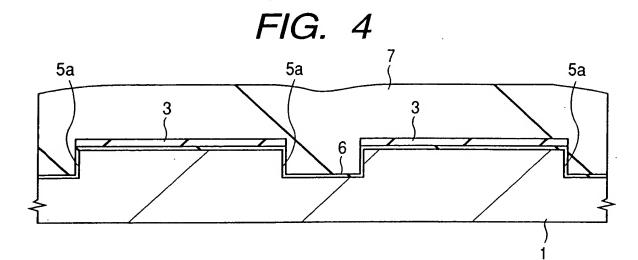


FIG. 5

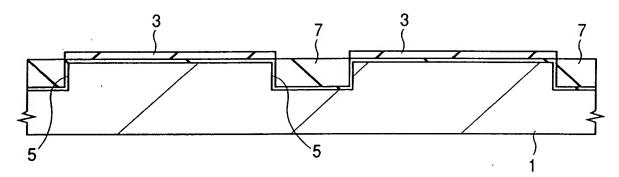


FIG. 6

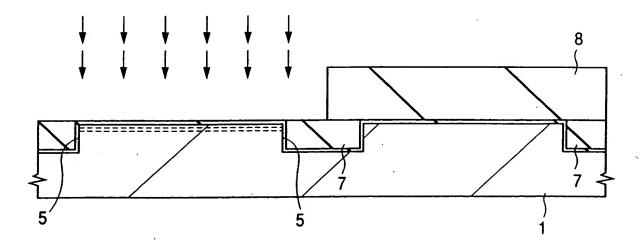


FIG. 7

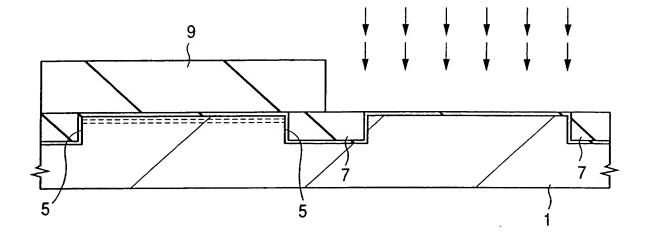


FIG. 8

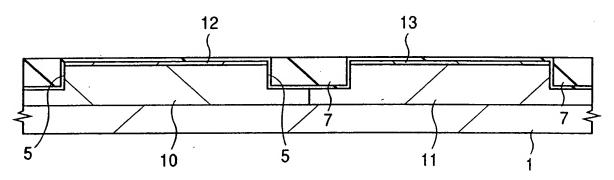
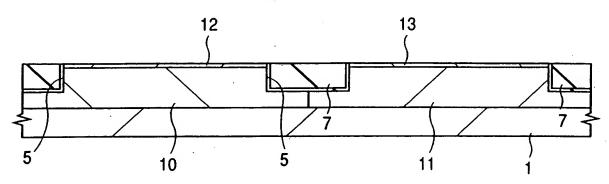


FIG. 10



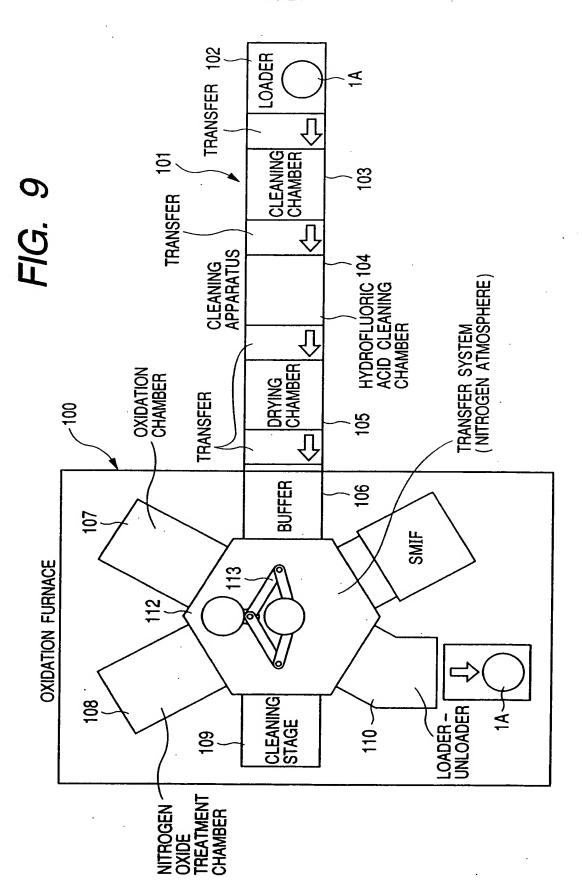
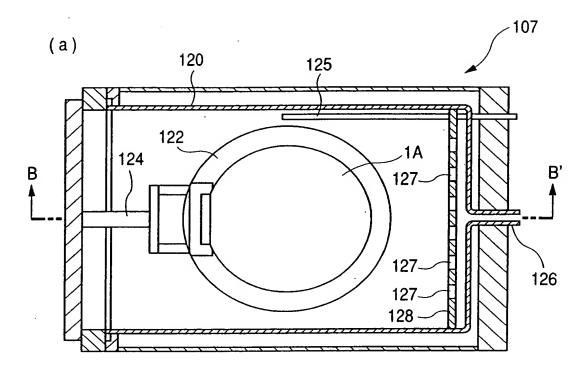


FIG. 11



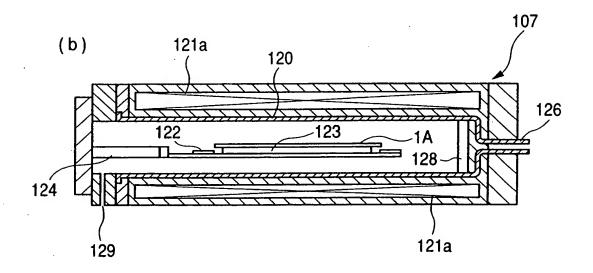
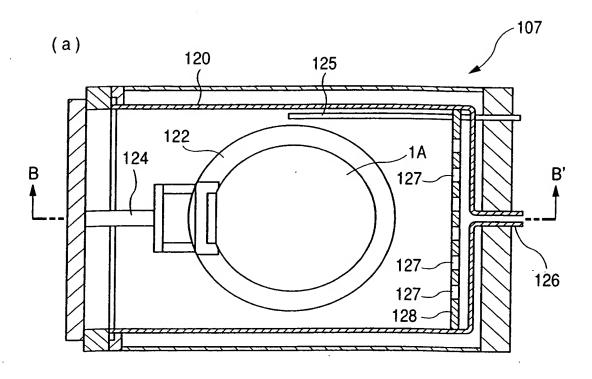
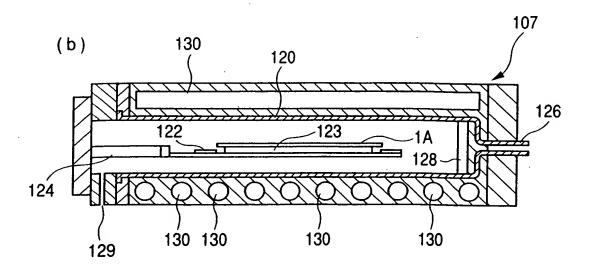
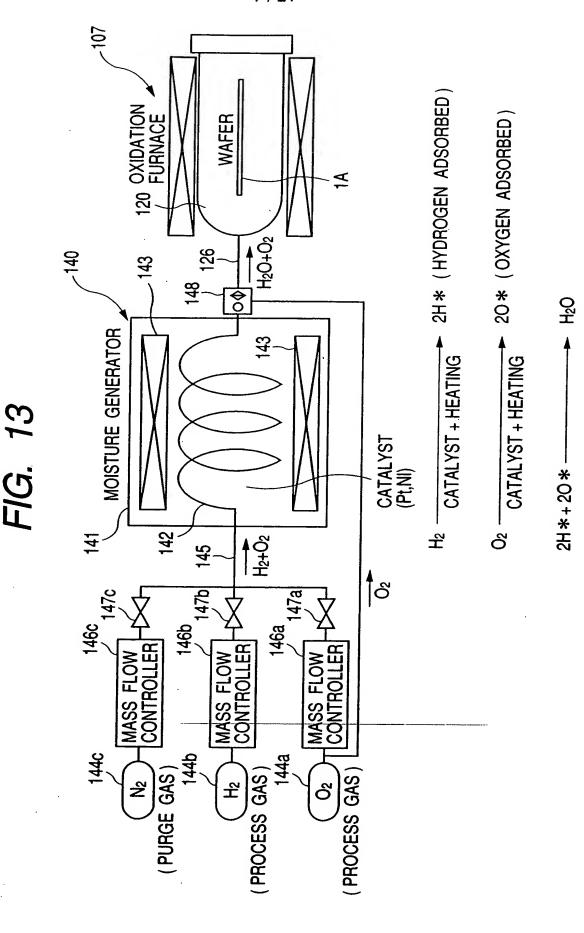


FIG. 12







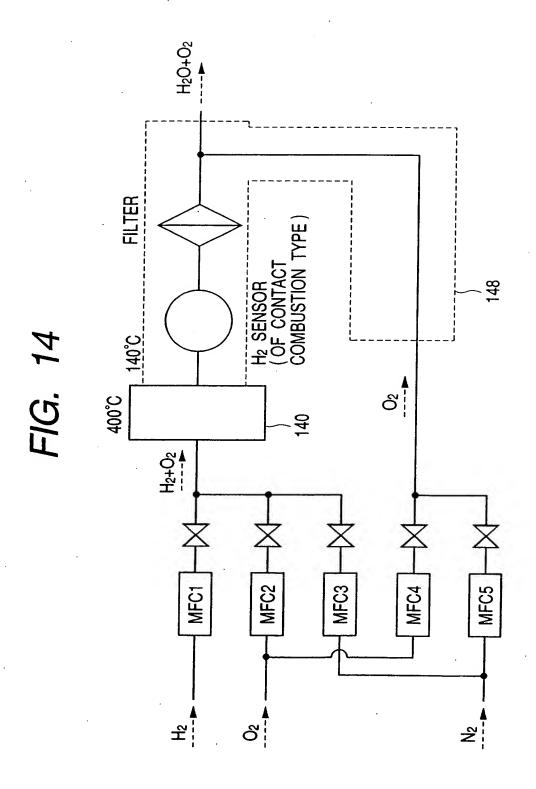


FIG. 15	WAFER	55"				٠				
	AFTER- PURGE	2' 20"								
	OXIDATION	ດໃ								
	H ₂ INTRODUCTION	15"								
	O ₂ PURGE	0 – 55"								
	N ₂ PURGE	-								
	WAFER	55"								
		TIME	2	FLOW RATE	O ₂ FLOW RATE		H ₂ FLOW RATE			

()()

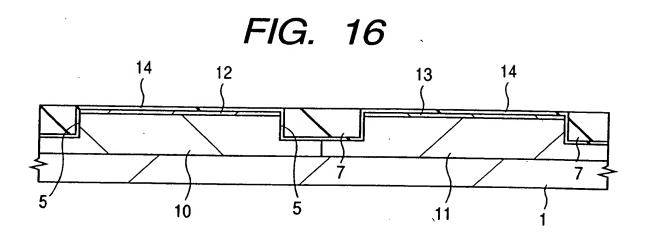


FIG. 17

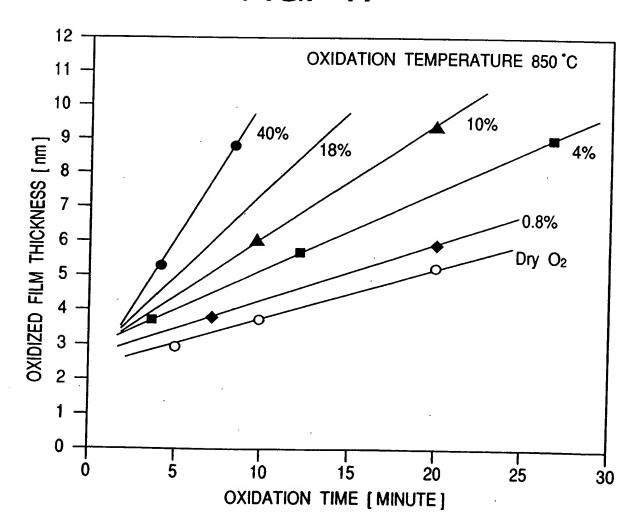
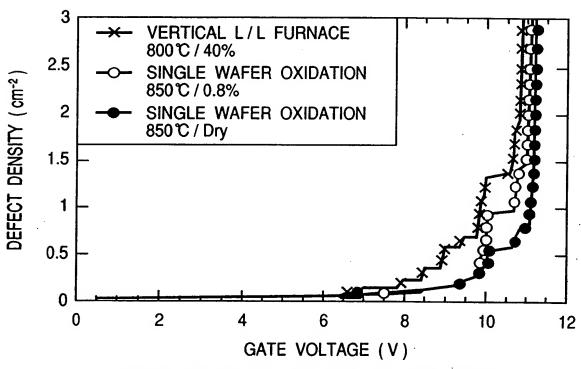


FIG. 18



INITIAL WITHSTAND VOLTAGE OF LOW MOISTURE CONTENT OXIDE FILM (OXIDE FILM THICKNESS = $9nm,S = 0.19cm^2$)

FIG. 19

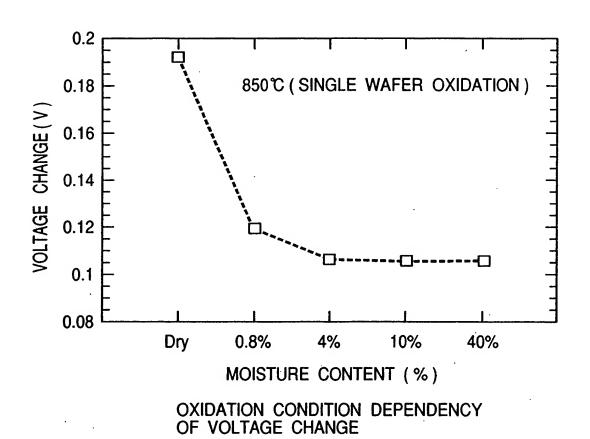
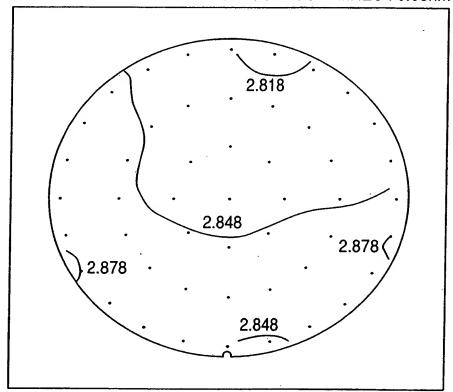


FIG. 20





WAFER DIAMETER: 8 inch

AVERAGE: 2.848 [nm]

MAX.: 2.881 [nm]

MIN.: 2.814 [nm]

MAX. – MIN. : 0.067 [nm]

±1.18[%]

TREATING CONDITIONS: 850°C, 2'30"

 $H_2/O_2: 0.05/4.9 \text{slm} \text{ (MOISTURE CONTENT}: 0.8\%)$ MEASUREMENT: AT 49 POINTS BY ELLIPSOMETER

FIG. 21

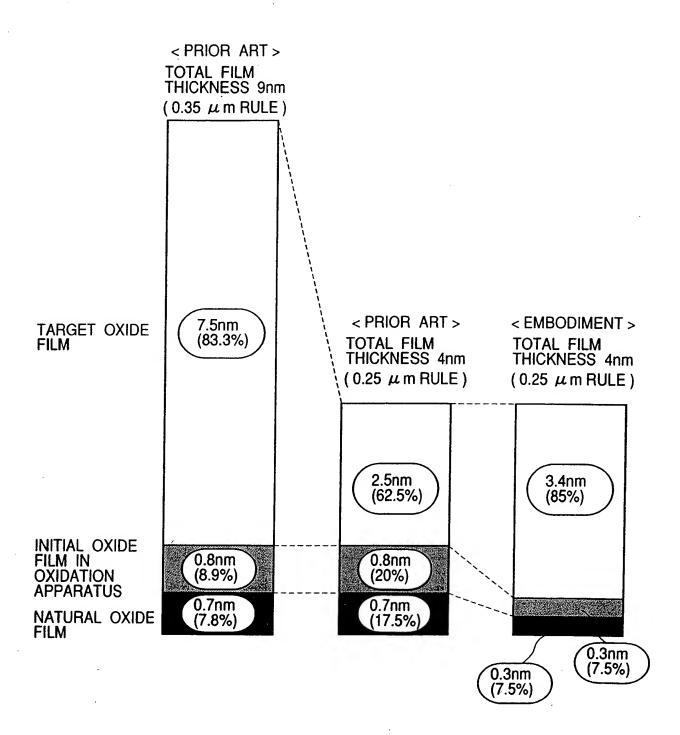
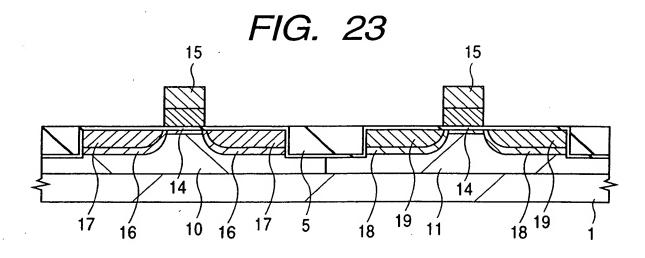


FIG. 22

15
14
7
7
11
11
11



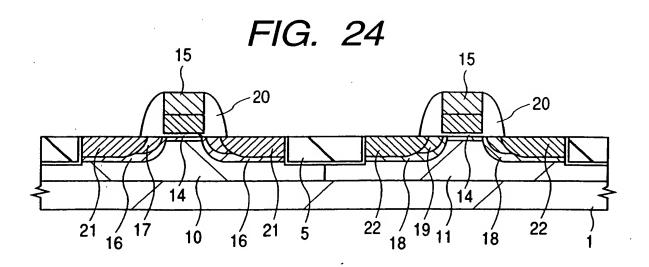


FIG. 25

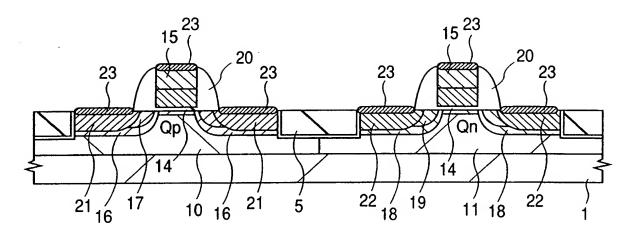


FIG. 26

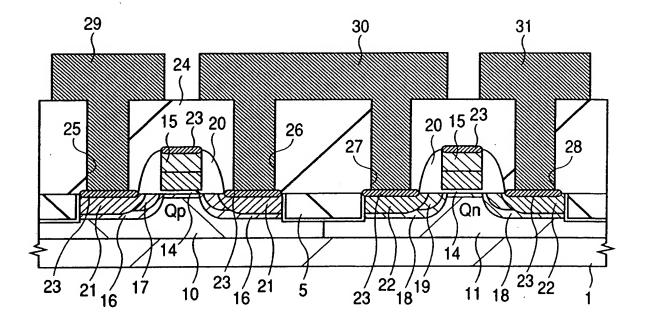


FIG. 27

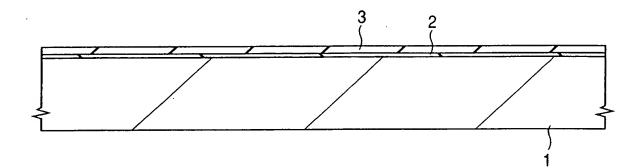


FIG. 28

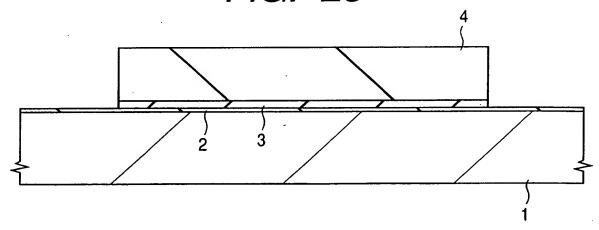


FIG. 29

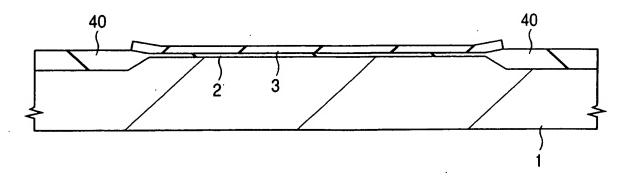
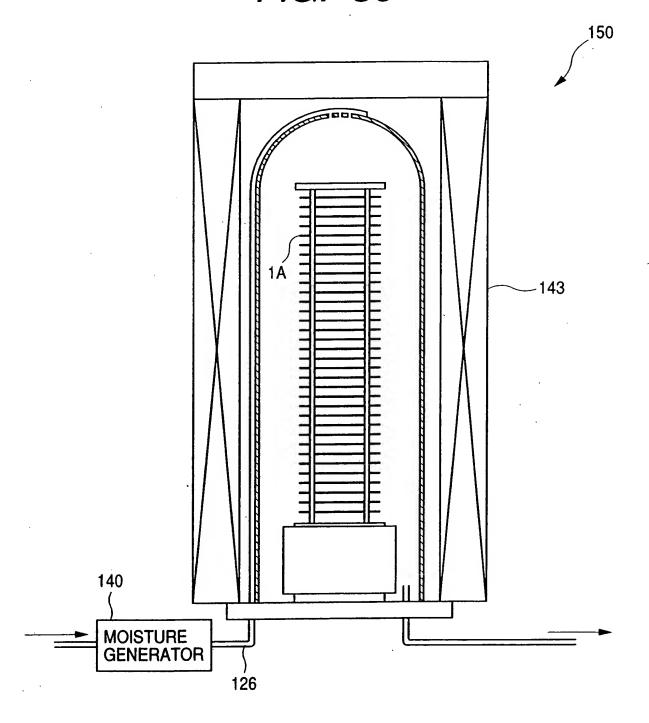
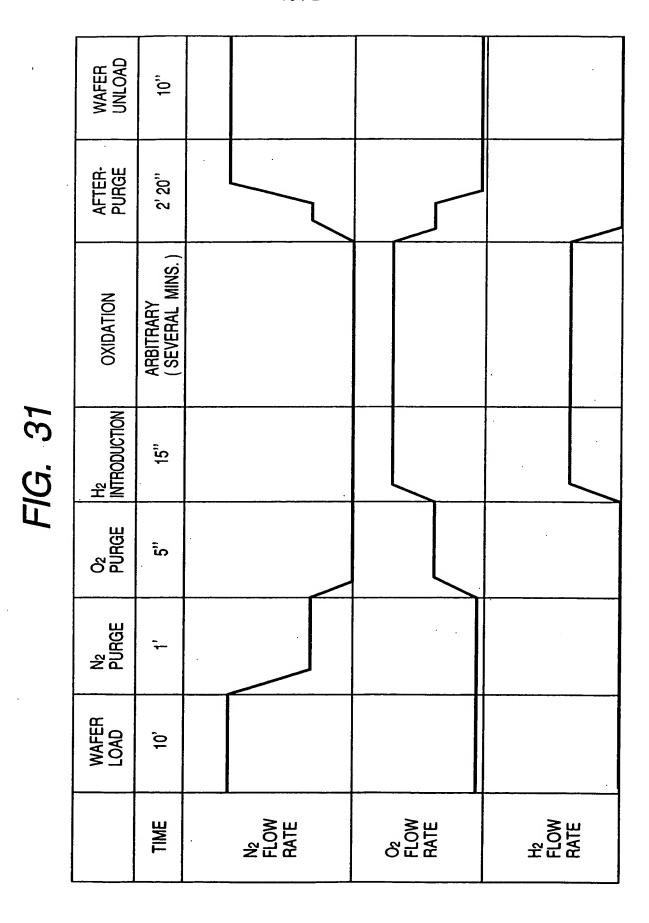


FIG. 30



()



(i)

FIG. 32

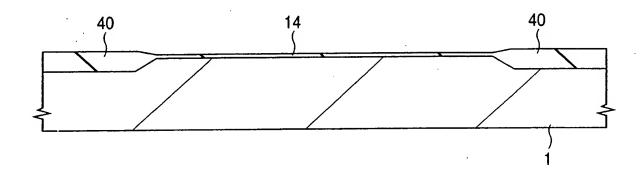
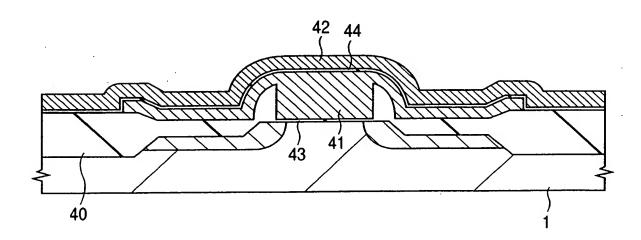
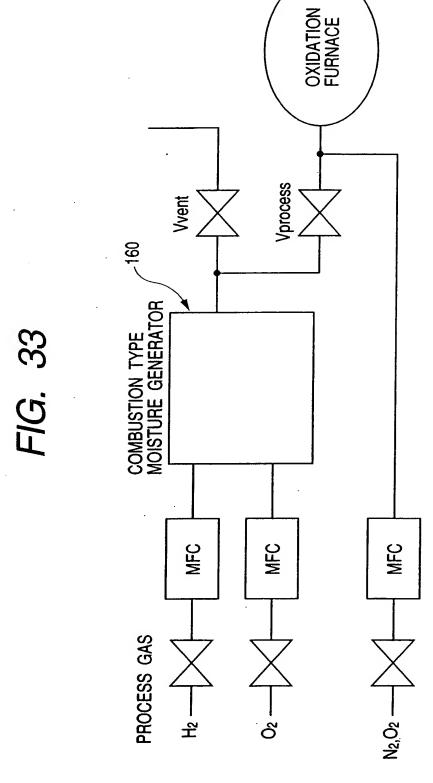


FIG. 34





21/21